Silicon PNP Power Transistors 2SA1355

DESCRIPTION

- With TO-220 package
- Low collector saturation voltage.
- Short switching time.

APPLICATIONS

- Various inductance lamp drivers for electrical equipment.
- Inverters, converters
- Power amplifier
- High-speed switching

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

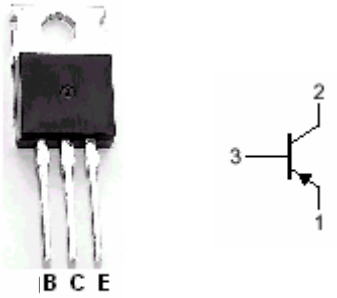

Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-70	V
V_{CEO}	Collector-emitter voltage	Open base	-70	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-4	A
P_C	Collector power dissipation	T_C=25℃	30	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-1mA ,I_E=0	-70			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-1mA ,I_B=0	-70			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-1mA ,I_C=0	-5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-2A; I_B=-0.2A			-0.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-2A; I_B=-0.2A			-1.2	V
I_{CBO}	Collector cut-off current	V_{CB}=-40V; I_E=0			-100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-4V; I_C=0			-100	μA
h_{FE}	DC current gain	I_C=-1A ; V_{CE}=-2V	70		280	
f_T	Transition frequency	I_C=-1A ; V_{CE}=-5V		40		MHz

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PACKAGE OUTLINE

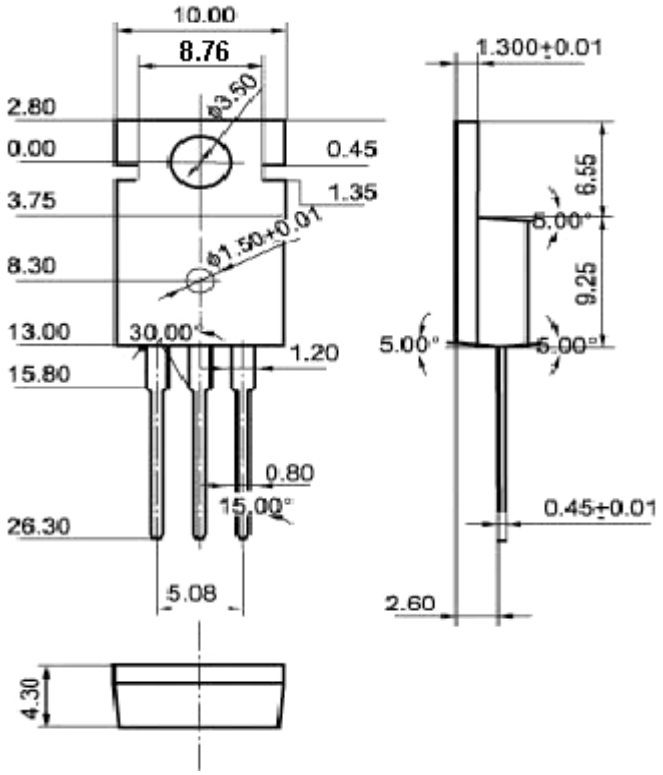

Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)